

SPM[™]

FSAB20PH60 Smart Power Module for Partial Switching Converter

Features

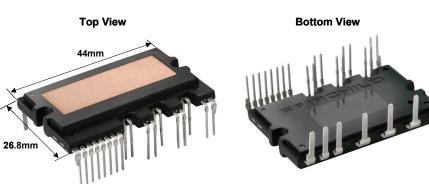
- · Very low thermal resistance due to using DBC
- 600V-20A single-phase rectifier bridge diode including two IGBTs for partial switching converter
- Integrated IC for gate driving and protection
- · Divided negative dc-link terminals for current sensing
- Isolation rating of 2500Vrms/min.

Applications

 AC 187V ~ 276V single-phase partial-switching converter of air-conditioner

General Description

FSAB20PH60 is an advanced smart power module of PSC(Partial Switching Converter) that Fairchild has newly developed and designed mainly targeting low-power application especially for an air conditioners. It combines optimized circuit protection and drive IC matched to IGBTs. System reliability is further enhanced by the integrated under-voltage lock-out and shortcircuit protection function.





Integrated Power Functions

· 600V-20A rectifiers for single-phase ac input with IGBT switches for operation of partial switching converter

Integrated Drive, Protection and System Control Functions

- For IGBTs: Gate drive circuit, Short circuit protection (SC) Control supply circuit under-voltage (UV) protection
- Fault signaling: Corresponding to a UV fault (Low-side supply)
- Input interface: 5V CMOS/LSTTL compatible, Schmitt trigger input
- · Built-in thermistor: Over-temperature monitoring

Pin Configuration

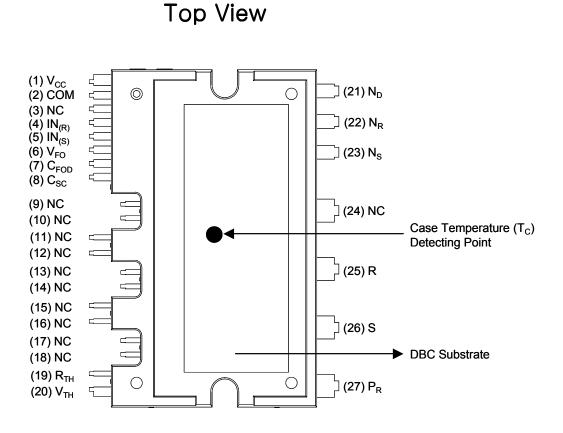
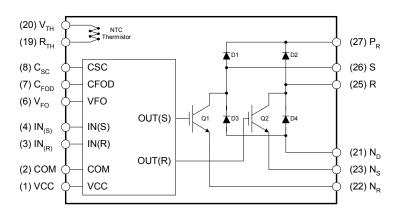


Figure 2.

Pin Number	Pin Name	Pin Description	
1	V _{CC}	Common Bias Voltage for IC	
2	СОМ	Common Supply Ground	
3	NC	Dummy Pin	
4	IN _(R)	Signal Input for R-phase IGBT	
5	IN _(S)	Signal Input for S-phase IGBT	
6	V _{FO}	Fault Output	
7	C _{FOD}	Capacitor for Fault Output Duration Time Selection	
8	C _{SC}	Capacitor (Low-pass Filter) for Short-Current Detection	
9	NC	Dummy Pin	
10	NC	Dummy Pin	
11	NC	Dummy Pin	
12	NC	Dummy Pin	
13	NC	Dummy Pin	
14	NC	Dummy Pin	
15	NC	Dummy Pin	
16	NC	Dummy Pin	
17	NC	Dummy Pin	
18	NC	Dummy Pin	
19	R _(TH)	Series Resistor for the Use of Thermistor (Temperature Detection)	
20	V _(TH)	Thermistor Bias Voltage	
21	N _D	Negative DC-Link of Rectifier Diode	
22	N _R	Negative DC-Link of R-phase IGBT	
23	N _S	Negative DC-Link of S-phase IGBT	
24	NC	Dummy Pin	
25	R	AC Input for R Phase	
26	S	AC Input for S Phase	
27	P _R	Positive DC-Link Output	

Internal Equivalent Circuit and Input/Output Pins



Note:

The low-side is composed of two IGBTs including rectifying diodes for each IGBT and one control IC which has gate driving, current sensing and protection functions. The highside is composed of two rectifying diodes without gate driving IC.

Figure 3.

FSAB20PH60 Smart Power Module for Partial Switching Converter

Absolute Maximum Ratings (T_J = 25°C, Unless Otherwise Specified)

Converter Part

Symbol Parameter		Conditions	Rating	Units
Vi	Input Supply Voltage	Applied between R-S	276	V
V _{i(Surge)}	Input Supply Voltage (Surge)	Applied between R-S	500	V
V _{PN}	Output Voltage	Applied between P-N	400	V
V _{PN(surge)}	Output Voltage (Surge)	Applied between P-N	500	V
V _{CES}	Collector-emitter Voltage	IGBT	600	V
V _{RRM}	Repetitive Peak Reverse Voltage	Diode	600	V
li	Input Current (100% Load)	$T_C \le 90^{\circ}C$, V_O = 280V, f_{PWM} = 60Hz	11	A _{RMS}
l _i	Input Current (130% Load)	$T_C \le 90^{\circ}C, V_O = 280V, f_{PWM} = 60Hz$	14	A _{RMS}
TJ	Operating Junction Temperature	(Note 1)	-20 ~ 125	°C

Note:

The maximum junction temperature rating of the power chips integrated within the module is 150 °C(@T_C ≤ 100°C). However, to insure safe operation, the average junction temperature should be limited to T_{J(ave)} ≤ 125°C (@T_C ≤ 100°C)

Control Part

Symbol	Parameter	Conditions	Rating	Units
V _{CC}	Control Supply Voltage	Applied between V _{CC} - COM	20	V
V _{IN}	Input Signal Voltage	Applied between $IN_{(R)}$, $IN_{(S)}$ - COM	-0.3~V _{CC} +0.3	V
V _{FO}	Fault Output Supply Voltage	Applied between V _{FO} - COM	-0.3~V _{CC} +0.3	V
I _{FO}	Fault Output Current	Sink Current at V _{FO} Pin	5	mA
V _{SC}	Current Sensing Input Voltage	Applied between C _{SC} - COM	-0.3~V _{CC} +0.3	V

Total System

Symbol	Parameter	Conditions	Rating	Units
Т _С	Module Case Operation Temperature	-20°C < T _J < 125°C, See Fig.2	-20 ~ 100	°C
T _{STG}	Storage Temperature		-40 ~ 125	°C
V _{ISO}	Isolation Voltage	60Hz, Sinusoidal, AC 1 minute, Connection Pins to DBC	2500	V _{rms}

Absolute Maximum Ratings

Thermal Resistance

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
R _{th(j-c)Q}	Junction to Case Thermal	Each IGBT under Operating Condition	-	-	2.8	°C/W
R _{th(j-c)D}	Resistance	Each Diode under Operating Condition	-	-	2.6	°C/W

Note:

2. For the measurement point of case temperature(T_C), please refer to Figure 2.

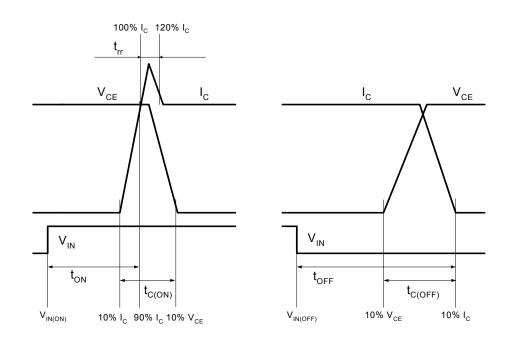
Electrical Characteristics (T_J = 25°C, Unless Otherwise Specified)

Main Circuit Part

Symbol	ltem	Condi	tions	Min.	Тур.	Max.	Units
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	V _{CC} = V _{BS} =15V V _{IN} = 5V	I _C = 6.5A, T _J = 25°C	-	2.1	2.6	V
V _{FM}	Diode Forward Voltage	V _{IN} = 0V	$I_{\rm C}$ = 20A, $T_{\rm J}$ = 25°C	-	1.1	1.5	V
t _{ON}	Switching Times	V _{PN} = 300V, V _{CC} = V _{BS} = 15V		-	0.48	-	μs
t _{C(ON)}		$I_{C} = 6.5A$ $V_{m} = 0V \leftrightarrow 5V$ Inducti	$V_{\rm IN}$ = 0V \leftrightarrow 5V, Inductive Load	-	0.85	-	μs
t _{OFF}		(Note 3)		-	0.56	-	μs
t _{C(OFF)}				-	0.10	-	μs
t _{rr}				-	1.35	-	μs
I _{CES}	Collector - Emitter Leakage Current	V _{CE} = V _{CES}		-	-	250	μA
I _R	Diode Leakage Current	V _R = V _{RRM}		-	-	250	μA

Note:

3. t_{ON} and t_{OFF} include the propagation delay time of the internal drive IC. $t_{C(ON)}$ and $t_{C(OFF)}$ are the switching time of IGBT itself under the given gate driving condition internally. For the detailed information, please see Figure 4.





Electrical Characteristics (T_J = 25°C, Unless Otherwise Specified)

Control Part

Symbol	Parameter	Co	onditions	Min.	Тур.	Max.	Units
I _{QCCL}	Quiescent V _{CC} Supply Current	V _{CC} = 15V IN _(L) = 0V	V _{CC(L)} - COM	-	-	23	mA
V _{FOH}	Fault Output Voltage	V _{SC} = 0V, V _{FO} Circu	uit: 4.7k Ω to 5V Pull-up	4.5	-	-	V
V _{FOL}		V _{SC} = 1V, V _{FO} Circu	uit: 4.7k Ω to 5V Pull-up	-	-	0.8	V
V _{SC(ref)}	Short Circuit Trip Level	V _{CC} = 15V (Note 4)		0.45	0.5	0.55	V
UV _{CCD}	Supply Circuit Under-	Detection Level	Detection Level		11.9	13.0	V
UV _{CCR}	Voltage Protection	Reset Level		11.2	12.4	13.2	V
t _{FOD}	Fault-out Pulse Width	C _{FOD} = 33nF (Note	5)	1.0	1.8	-	ms
V _{IN(ON)}	ON Threshold Voltage	Applied between IN	_(R) , IN _(S) - COM	3.0	-	-	V
V _{IN(OFF)}	OFF Threshold Voltage	1		-	-	0.8	V
R _{TH}	Resistance of Thermistor	@ T _C = 25°C (Note Fig. 10)		-	50	-	kΩ
		@ T _C = 80°C (Note	Fig. 10)	-	5.76	-	kΩ

Note:

4. Over current protection is functioning only for the low-side IGBT.

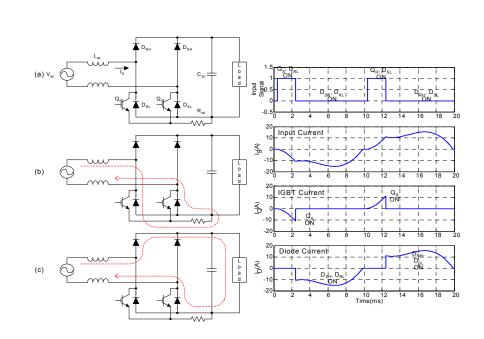
5. The fault-out pulse width t_{FOD} depends on the capacitance value of C_{FOD} according to the following approximate equation : C_{FOD} = 18.3 x 10⁻⁶ x $t_{FOD}[F]$

Recommended Operating Conditions

Symbol	Parameter	Condition	Value			Units
Symbol	Falailletei	Condition	Min.	Тур.	Max.	Units
Vi	Input Supply Voltage	Applied between R - S	187	-	276	V _{rms}
V _{PN}	Output Voltage	Applied between P - N	-	280	400	V
V _{CC}	Control Supply Voltage	Applied between V _{CC} - COM	13.5	15	16.5	V
f _{PWM}	PWM Input Signal	$T_C \leq 100^{\circ}C, T_J \leq 125^{\circ}C, \text{Per IGBT}$ (Note 6)	-	60	-	Hz

Note:

6. Regarding the switching method of FSAB20PH60, it follows the control method of the typical partial-switching power factor correction circuit as shown in Figure 5.



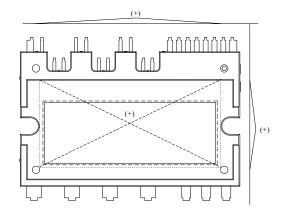
Note:

 Q_R or Q_S depending on the polarity of input voltage V_{ac} , is turned on at the zero crossing point of input voltage, and turned off considering the output power and distortion of input current. Each IGBT turns on with zero current with the utility frequency, 50 or 60Hz.

Figure 5. PWM Example of FSAB20PH60

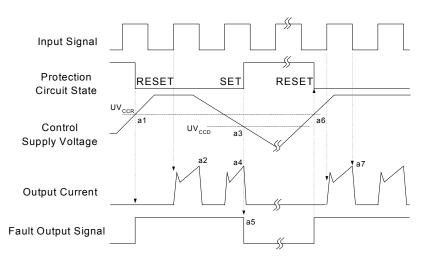
Mechanical Characteristics and Ratings

Parameter	Co	nditions	Limits Min. Typ. Max.			- Units	
Falameter		nunions					
Mounting Torque	Mounting Screw: M3	Recommended 0.62Nm	0.51	0.62	0.72	N∙m	
Heatsink Flatness		Note Fig. 6	0	-	120	μm	
Weight			-	15.00	-	g	



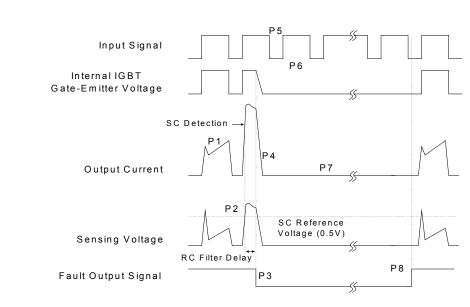


Time Charts of SPMs Protective Function



- a1 : Control supply voltage rises: After the voltage rises UV_{CCR} , the circuits start to operate when next input is applied.
- a2 : Normal operation: IGBT ON and carrying current.
- a3 : Under voltage detection (UV $_{\mbox{CCD}}$).
- a4 : IGBT OFF in spite of control input condition.
- a5 : Fault output operation starts.
- a6 : Under voltage reset (UV_{CCR}).
- a7 : Normal operation: IGBT ON and carrying current.

Figure 7. Under-Voltage Protection



(with the external shunt resistance and CR connection)

c1 : Normal operation: IGBT ON and carrying current.

c2 : Short circuit current detection (SC trigger).

c3 : Hard IGBT gate interrupt.

c4 : IGBT turns OFF.

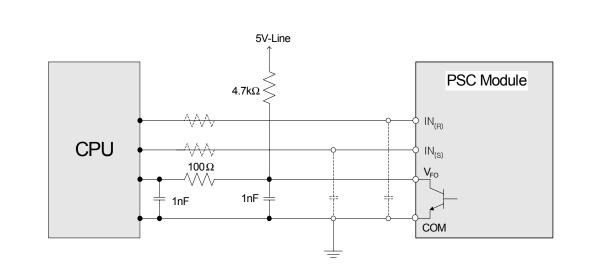
c5 : Fault output timer operation starts: The pulse width of the fault output signal is set by the external capacitor C_{FO} .

c6 : Input "L" : IGBT OFF state.

c7 : Input "H": IGBT ON state, but during the active period of fault output the IGBT doesn't turn ON.

c8 : IGBT OFF state

Figure 8. Over Current Protection



Note:

- 1. RC coupling at each input (parts shown dotted) might change depending on the PWM control scheme used in the application and the wiring impedance of the application's printed circuit board. The SPM input signal section integrates 3.3kΩ (typ.) pull-down resistor. Therefore, when using an external filtering resistor, please pay attention to the signal voltage drop at input terminal.
- 2. The logic input is compatible with standard CMOS or LSTTL outputs.

Figure 9. Recommended CPU I/O Interface Circuit



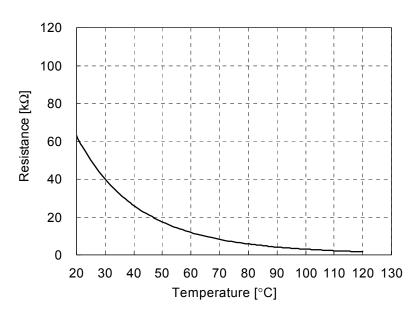
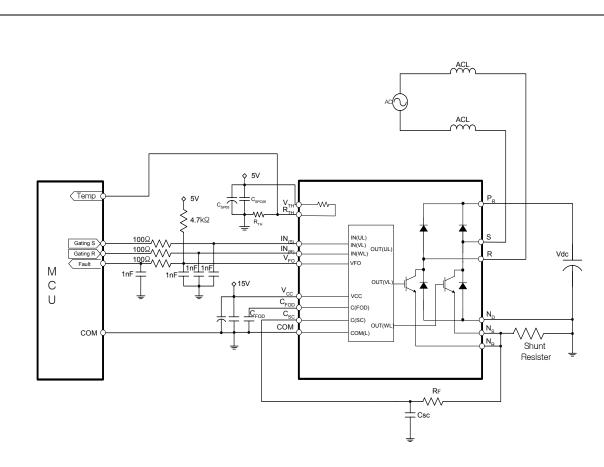


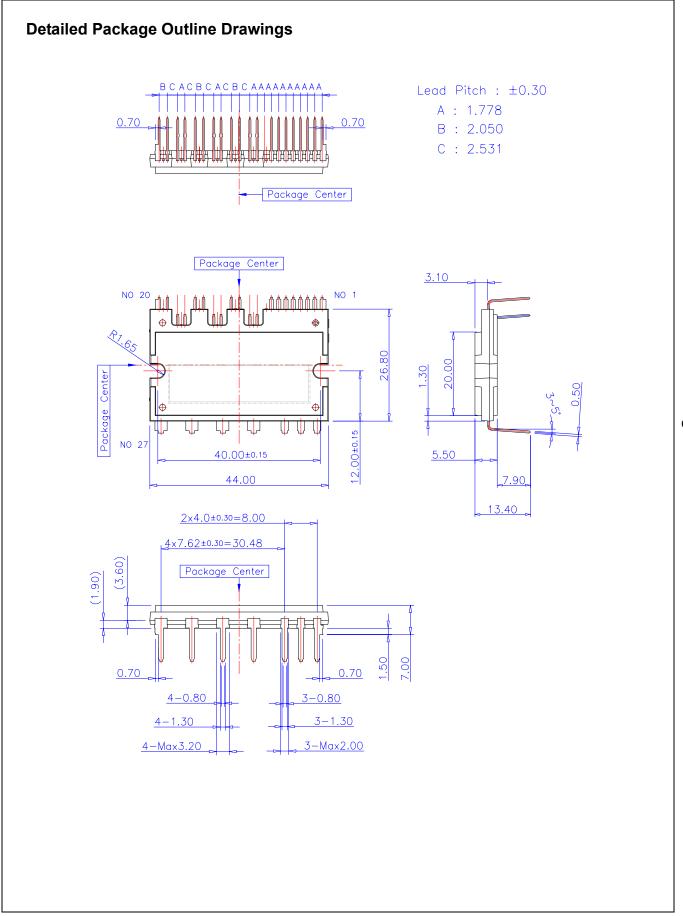
Figure 10. R-T Curve of the Built-in Thermistor

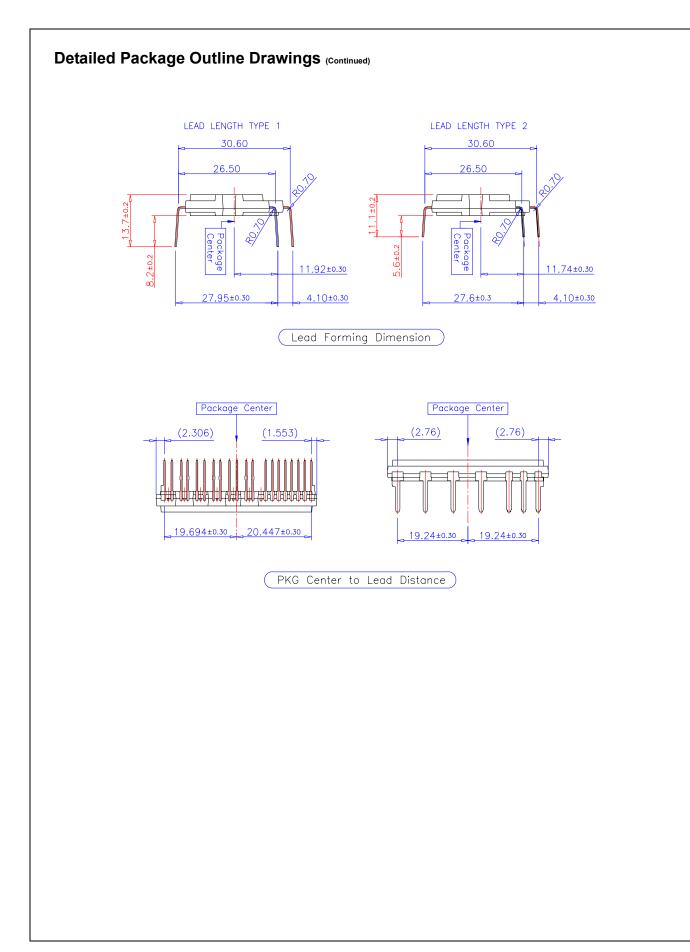


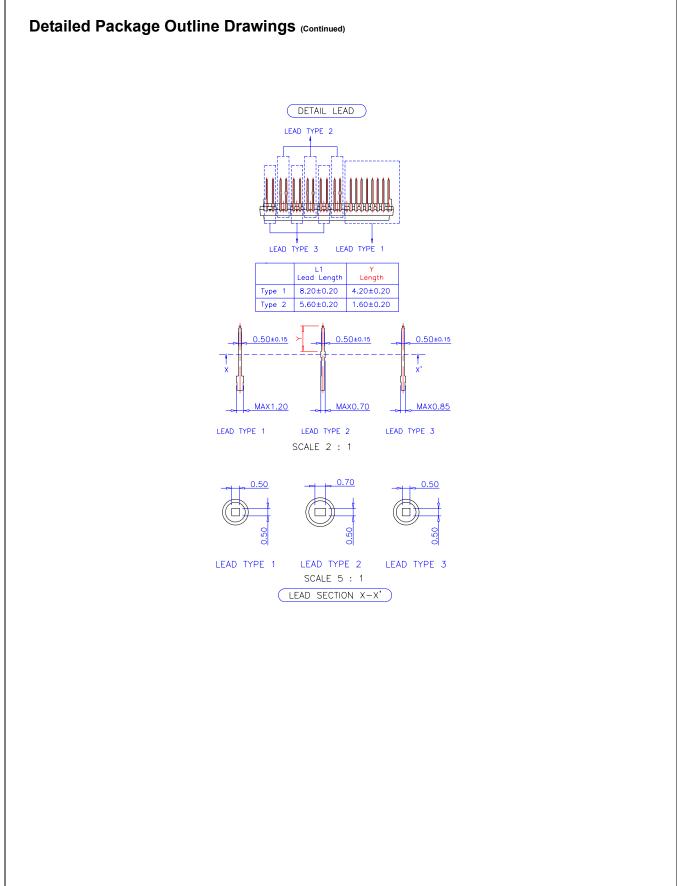
Note:

- 1. To avoid malfunction, the wiring of each input should be as short as possible. (less than 2-3cm)
- 2. V_{FO} output is open collector type. This signal line should be pulled up to the positive side of the 5V power supply with approximately 4.7k Ω resistance. Please refer to Figure 8.
- 3. V_{FO} output pulse width should be determined by connecting an external capacitor(C_{FOD}) between C_{FOD} (pin7) and COM(pin2). (Example : if C_{FOD} = 33 nF, then t_{FO} = 1.8ms (typ.)) Please refer to the note 6 for calculation method.
- 4. Input signal is High-Active type. There is a 3.3kΩ resistor inside the IC to pull down each input signal line to GND. When employing RC coupling circuits, set up such RC couple that input signal agree with turn-off/turn-on threshold voltage.
- 5. To prevent errors of the protection function, the wiring around $\mathsf{R}_{SC}, \mathsf{R}_{F}$ and C_{SC} should be as short as possible.
- 6. In the over current protection circuit, please select the $R_F C_{SC}$ time constant in the range 3~4 $\mu s.$
- 7. Each capacitor should be mounted as close to the pins as possible.
- 8. Relays are used at almost every systems of electrical equipments of home appliances. In these cases, there should be sufficient distance between the CPU and the relays.

Figure 11. Application Circuit







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